

**Programme of the 6th Solid State Surfaces and Interfaces,
24 November to 27 November, 2008, Smolenice Castle, Slovakia**

Monday, 24 November 2008			
09:30 - 13:30	Registration		
13:30 - 13:40	Opening		
Chairman:	Prof. G.P. Srivastava		
13:40 - 14:30	H. Kobayashi	One-step and two-step NAOS methods for fabrication of SiO ₂ /Si structure with excellent electrical characteristics	Institute of Scientific and Industrial Research, Osaka University, and CREST, Japan Science and Technology Agency, Osaka, Japan
14:30 - 15:20	H. Angermann	Wet-chemical passivation and electronic interface properties of Silicon substrates	Helmholtz-Zentrum Berlin für Materialien und Energie, Berlin, Germany
15:20 - 15:35	Coffee break		
15:35 - 16:25	A. Larrea	Interfaces and properties in directionally solidified eutectics for the efficient use of energy	Instituto de Ciencia de Materiales de Aragon, Centro Politecnico Superior, Edificio Torres Quevedo, Zaragoza, España
16:25 - 16:50	S. Jurečka	On topographic and optical properties of SiC/SiO ₂ surfaces	Department of Engineering Fundamentals, FEE ŽU, Liptovský Mikulas, Slovak Republic
16:50 - 17:05	Coffee break		
17:05 - 17:55	T. Chasse	Orientation and electronic properties of organic molecules on metallic substrates - distinguishing between first layers and thin films	Universität Tübingen, Institut für Physikalische und Theoretische Chemie, Tübingen, Germany
17:55 - 18:20	T. Nakazawa	Nano structure of low crystallinity carbon materials analyzed by using high energy X-ray diffraction	Nagano National College of Technology, Nagano, Japan
18:20 - 18:45	O. Babchenko	Nanostructuring of diamond films using self-assembled nanoparticles	Institute of Physics, Academy of Sciences of the Czech Republic, Prague, Czech Republic
19:30 - 22:30	Welcome party with live folk music (music group Červeník)		

Tuesday, 25 November 2008			
7:30 - 8:30	Breakfast		
Chairman:	Prof. H. Kobayashi		
8:30 - 9:20	G.P. Srivastava	Theoretical Modelling of Surface Phonons	School of Physics, University of Exeter, Exeter, United Kingdom
9:20 - 10:10	J. Szuber	GaAs surface cleaning by atomic hydrogen	Department of Electron Technology, Silesian University of Technology, Gliwice, Poland
10:10 - 10:25	Coffee break		
10:25 - 11:15	Š. Luby	Role of interfaces in GMR layered structures	Institute of Physics, Slovak Academy of Sciences, Bratislava, Slovakia
11:15 - 12:05	Z.Lj. Petrovič	Basic Phenomena and Data for Modelling of Interactions Between Surfaces and Gas Discharges	Institute of Physics, University of Belgrade, Zemun, Serbia
12:05 - 12:30	A. Vincze	Surface and interface properties of thin parylene and pentacene layers	International Laser Centre, Bratislava, Slovakia
12:30 - 13:30	Lunch		
Chairman:	Prof. T. Chasse		
13:30 - 14:20	G. Pepe	Novel material solutions for superconductive ultrafast photodetectors	Universita di Napoli Federico II, Facolta di Ingegneria, Napoli, Italy
14:20 - 14:45	Nemeth	Oscillation and hysteresis of the reactive plasma during ZnO deposition	Hungarian Academy of Sciences, Research Institute for Technical Physics and Materials Science, Budapest, Hungary
14:45 - 15:00	Coffee break		
15:00 - 15:25	P. Bury	Acoustic spectroscopy of Si/SiO ₂ structures with ultrathin SiO ₂ layers formed with nitrid acid oxidation	Department of Physics, Faculty of Electrical Engineering, University of Žilina, Žilina, Slovakia
15:25 - 15:50	J. Bočan	Pulsed laser treatment of gold and black gold thin films fabricated by thermal evaporation	Institute of Physics, Academy of Sciences of the Czech Republic, Prague, Czech Republic
15:50 - 16:15	D. Haško	The effects of oxygen pressure on the structure of ZnO layers prepared by pulsed laser deposition from Zn and ZnO targets	International Laser Centre, Bratislava, Slovakia
16:30	Departure of bus for visit of opera performance in Bratislava (Slovak National Theatre G. Donizetti: Lucrezia Borgia). Participants will receive dry supper.		
18:30	Supper		
23:15	Supposed return of Bratislava		

Wednesday, 26 November 2008

7:30 ♦ 8:30	Breakfast		
Chairman:	Prof. A. Plecenik		
8:30 - 9:20	M. Belogolovskii	Interface resistive switching and memory effects in manganites	Donetsk Physical and Technical Institute, National Academy of Sciences of Ukraine, Ukraine
9:20 - 10:10	R.S. Gonnelli	Point-contact Andreev-reflection spectroscopy in novel Fe-based superconductors $\text{LaFeAsO}_{1-x}\text{F}_x$ and $\text{SmFeAsO}_{0.8}\text{F}_{0.2}$	CNISM and Politecnico di Torino, Torino, Italy
10:10 - 10:25	Coffee break		
10:25 - 11:15	E. Ilichev	Sisiphus cooling and amplification by a superconducting qubit	Institute for Physical High Technology, Jena, Germany
11:15 - 12:05	Š. Chromik	Perovskite YBCO and LSMO films on advanced semiconducting substrates	Institute of Electrical Engineering SAS, Bratislava, Slovakia
12:15 - 13:30	Lunch		
Chairman:	Prof. J. Szuber		
13:30 - 14:20	A. Kasikov	Sensitizing Cr_2O_3 thin films for resistive gas sensors by Pt coating	Institute of Physics, University of Tartu, Tartu, Estonia
14:20 - 15:10	F. Fettaf	Perpendicular anisotropy in magnetic layers: role of oxidation in Pt/Co/AlO_x	CNRS Institut Neel, Grenoble France
15:10 - 15:35	J. Mullerová	Optical absorption in PECVD deposited thin hydrogenated silicon in light of ordering effects	Department of Engineering Fundamentals, FEE ŽU, Liptovský Mikuláš, Slovak Republic
15:35 - 15:50	Coffee break		
15:50 - 16:40	Zs. J. Horváth and P. Basa	Semiconductor nanocrystals in dielectrics: preparation and characterization	Hungarian Academy of Sciences, Research Institute for Technical Physics and Materials Science, Budapest Hungary
16:40 - 17:05	L. Skatkov	Peculiarities on Change Structure and Properties of Nb_2O_5 Dielectric Films due to Generating Defects on their Surface	PCB "Argo", Beer Sheva, Israel
17:05 - 17:30	B. Bohunický	State of art scanning electron microscopy and focus ion beam analytical techniques	KVANT Comp., Bratislava, Slovakia
17:30 - 19:00	Poster session		
19:00 - 22:00	Picnic with draft beer		

Thursday, 27 November 2008

7:30 - 8:30	Breakfast		
Chairman:	Dr. H. Angermann		
8:30 - 9:20	M. Takahashi	Passivation of defect states in surface and edge regions on pn-junction Si solar cells by use of hydrogen cyanide solutions	ISIR, Osaka University and CREST, Japan Science and Technology Agency, Osaka, Japan
9:20 - 10:10	M.I. Tsindlekht	Low Frequency Dynamics of Surface Superconducting States in Tilted Magnetic Fields	The Racah Institute of Physics, The Hebrew University of Jerusalem, Jerusalem, Israel
10:10 - 10:25	Coffee break		
10:25 - 11:15	H. Wulff	Plasma chemical reactions in thin nickel layers	Institute for Chemistry and BioChemistry, University of Greifswald, Greifswald, Germany
11:15 - 12:05	D. Basa	Plasma treatment studies of MIS devices	Department of Physics, Utkal University, Bhubaneswar, India
12:05 - 12:55	D. Velič	From Surface, through Interface in Time - Secondary Ion Mass Spectrometry and Laser Spectroscopy	International Laser Center, Bratislava, Slovakia and Faculty of Natural Sciences, Comenius University, Bratislava, Slovakia
12:55 - 13:00	Conclusion		
13:00 - 13:45	Lunch		
13:45	Conference bus departure to Bratislava (bus station and railway station)		

Poster contributions

1	B. Bohunický	State of art scanning electron microscopy and focus ion beam analytical techniques	KVANT Comp., Bratislava, Slovakia
2	R. Brunner	Non-gaussian photoluminescence peaks of thin a-Si:H layers	Institute of Physics SAS, Bratislava, Slovakia
3	M. Davydova	Influence of deposition temperature on growth of carbon nanotubes by capacitively coupled rf plasma process	Institute of Physics ASCR, Prague, Czech Republic
4	M. Mikula	High barrier SiO _x layers on flexible plastic foils	Faculty of Chemical and Food Technology, STU, Bratislava, Slovakia
5	Zs.J. Horváth	Si and Ge nanocrystals in SiO ₂ and SiN _x - an interplay of thin layers	Hungarian Academy of Sciences, Research Institute for Technical Physics and Materials Science, Budapest, Hungary
6	Zs.J. Horváth	Electrical behaviour of light and heavy water vapour treated Al/SiO _x N _y /Si structures prepared by rapid thermal processing	Hungarian Academy of Sciences, Research Institute for Technical Physics and Materials Science, Budapest, Hungary
7	Y. Ikka	Change of band bending of n-Si(100) surface by cyanide treatment	ISIR, Osaka University, Osaka, Japan
8	S. Imai	HNO ₃ concentration dependence of electrical characteristics of SiO ₂ /Si structure formed by NAOS method	Display Technology Development Group, Sharp Corporation, Nara, Japan
9	M. Krč	Introduction of amino groups on polymer surface using microwave surface-wave plasma	Institute of Physics Slovak Academy of Science, Bratislava, Slovakia
10	M. Kopáni	FTIR properties of ultrathin and very thin silicon oxide layers	Faculty of Medicine, Comenius University, Bratislava, Slovakia
11	M. Madani	SiC cleaning method by use of dilute HCN aqueous solutions	Institute of Scientific and Industrial Research, Osaka University, and CREST, Japan Science and Technology Agency, Osaka, Japan
12	E. Malinovský	On the temperature dependence of the dissociative recombination of Ne ₂ ⁺ ions with electrons	Institute of Physics, Slovak Academy of Sciences, Piešťany, Slovakia
13	J. Nápravník	Application of SnAcAc/Pt multilayers prepared by Pulsed Laser Deposition method for gas detection	Department of Solid State Technology, Prague, Czech Republic
14	E. Pinčík	On Electrical, Optical and Structural Properties of Si-based Structures I	Institute of Physics of SAS, Bratislava, Slovakia
15	E. Pinčík	On Electrical, Optical and Structural	Institute of Physics of SAS,

		Properties of Si-based Structures II	Bratislava, Slovakia
16	J. Rusnák	Investigation of very thin SiO ₂ /Si structures by charge version of DLTS using small excitation voltage steps	Institute of Physics of SAS, Bratislava, Slovakia
17	P. Schlosser	Effect of preparation condition on gas sensitivity of TiO ₂ thin films	Faculty of Mathematics, Physics and Informatics, Comenius University, Bratislava, Slovakia
18	T. Yanase	SiO ₂ /Si structure fabrication at low temperature by novel nitric acid method	ISIR, Osaka University and CREST, Japan Science and Technology Agency, Osaka, Japan
19	A. Dujavov	will be specified later	Institute of Electrical Engineering SAS, Bratislava, Slovakia